TECHNICAL DATA DATA SHEET 5580 REV. -

HERMETIC ULTRA FAST SOFT RECOVERY RECTIFIER

Features:

- Low forward voltage drop
- Low power loss, high efficiency
- Very high surge capacity
- Soft reverse recovery at low and high temperature
- Trr guaranteed lower than 50 nsec
- Electrically / mechanically stable during and after packaging

Maximum Ratings:

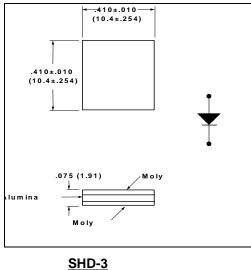
Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	300	V
Max. Average Forward Current	I _{F(AV)}	50% duty cycle, rectangular wave form, T _C = 65 °C	60	Α
Max. Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	8.3 msec, sine pulse	720	А
Thermal Impedance	Z_{TH}	T _C = 25 °C	0.5	°C / W
Max. Junction Temperature	TJ	-	- 65 to + 150	°C
Max. Storage Temperature	T _{stg}	-	- 65 to + 150	°C

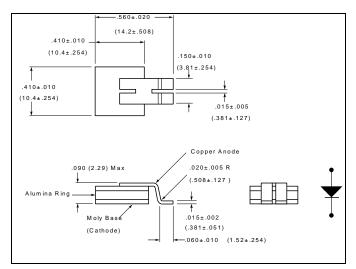
Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 20A, Pulse, T _J = 25 °C	0.85	0.93	V
		@ 60A, Pulse, T _J = 25 °C	1.02	1.12	
	V_{F2}	@ 20A, Pulse, T _J = 125 °C	-	0.82	V
		@ 60A, Pulse, T _J = 125 °C	-	1.05	
	I _{R1}	$@V_R = 300V, Pulse, T_J = 25 °C$	2	30	μΑ
Max. Reverse Current	I _{R2}	$@V_R = 300V, Pulse, T_J = 125 °C$	-	300	μΑ
Reverse Recovery Time	t _{RR}	$I_F = 0.5A$; $I_R = 1.0A$, $I_{RM} = 0.25A$	45	55	nsec
$T_J = 25 ^{\circ}C$		$I_F=20A$, di/dt =100A/ μ s, V_R =100V	51	60	
Max. Junction Capacitance	C _T	$@V_R = 10V, T_C = 25 ^{\circ}C$	400	-	рF
		$f_{SIG} = 1MHz,$			
		$I_{SIG} = 100 \text{mV (p-p)}$			

TECHNICAL DATA
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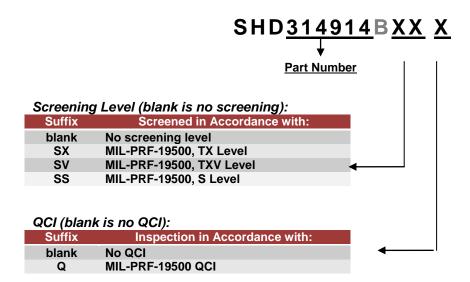
MECHANICAL DIMENSIONS: In Inches / mm





SHD-3B

PART ORDERING INFORMATION:





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